A Method to Control Palladium Crystallographic Texture and Surface Morphology

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Abstract

Statistical studies performed at SRI (1) and ENEA (2) have identified a potential threshold deuterium loading (D/Pd ~0.9), surface texture {100}<01>, and surface morphology that give the highest probability to observation of the Fleischman-Pons excess heat effect using palladium foils. The development of crystallographic texture, grain size distribution, and rate of recrystallization are controlled by many factors. The surface morphology that develops during strong acid etching is strongly influenced by the thickness of the type of oxide layer that forms during recrystallization and subsequent cooling. This paper will report on annealing, oxidation and etching procedures to produce foils with desired crystallographic texture, surface morphology, strong grain boundary grooving, and the apparent discount between metallurgical treatment treatments and hydrogen loading.

- [1] McKubre, M.C.H. and F.L. Tanzella, "Using resistivity to measure H/Pd and D/Pd loading: method and significance", The 12th International Conference on Condensed Matter Nuclear Science. 2005. Yokohama, Japan.
- [2] Violante, V., et al., "The Study of the Fleischman and Pons Effect through the Materials Science Development", J. Condensed Matter Nucl. Sci., 2012. 8.



Study to Produce Strong Cube Texture Pd Foils Production

D.L Knies, R. Cantwell, O. Dmitriyeva, G. Stanish, E. Goulet, S. Hamm and M. McConnell

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Motivation

After nearly three years, the production of over 300 cathodes, and 35,000+ hours of run time, Coolescence LLC has been unable to reproduce the excess heat effect. To improve our chances of seeing the effect, we decided to take a step back and try to gain control of a number of specific material properties of pure palladium foils thought to play a crucial role:

- **✓** Texture (crystalline) dominant <100> crystallographic orientation
- ✓ Pronounces peaks in the Power Spectral Density Function between 10⁴ and 10⁷ m⁻¹ "Labyrinthic Surface"
- ✓ Mean grain size ~100 µm with well-defined grain boundary grooving
- **✓** Capable of exceeding D/Pd "Threshold"

(D concentration >0.9 atomic faction with low current density "Easy Loading")

✓ Capable of supporting high flux across the cathode/electrolyte boundary

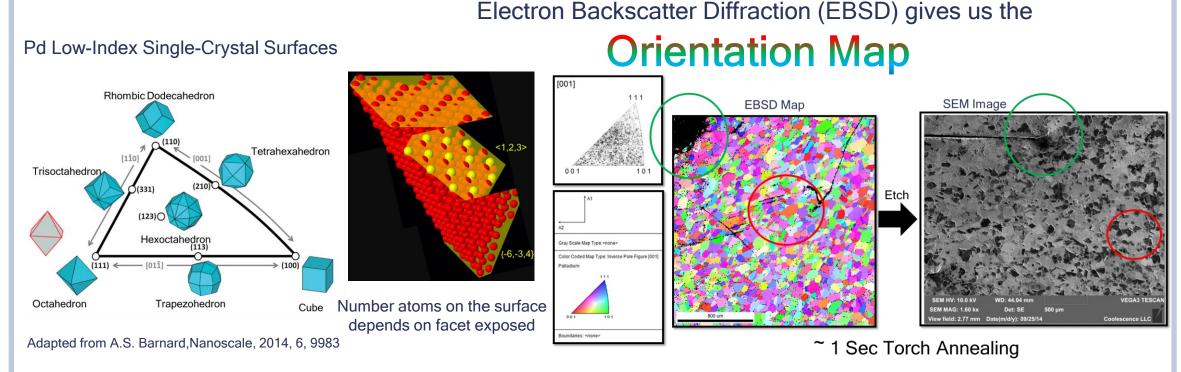


^[2] M. McKubre, et al., in Frontier of Cold Fusion, Proc. ICCF3, H. Ikegami (Ed.), UAP, Tokyo, 1993, pp. 5-19.



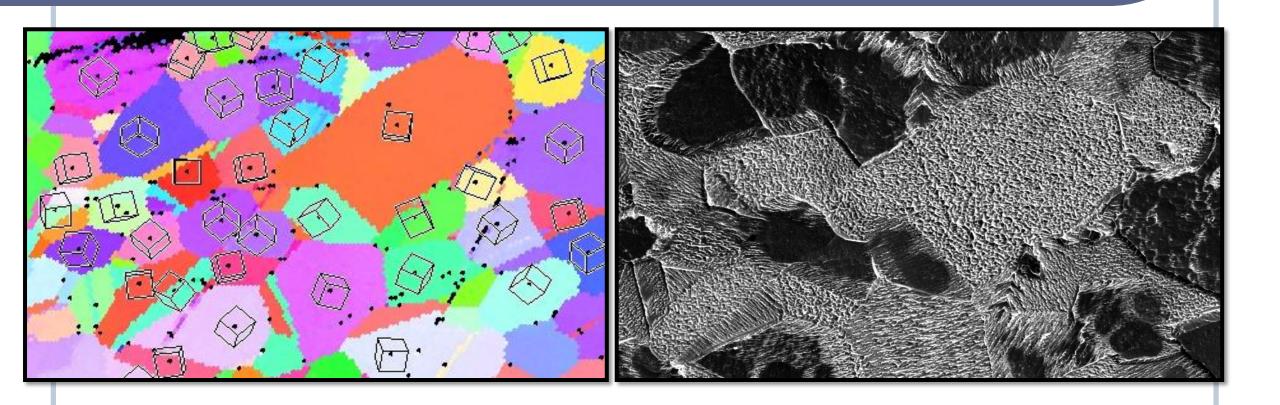
^[3] K. Kunimatsu, et al., in Frontiers of Cold Fusion, Proc. ICCF3, H. Ikegami (Ed.), UAP, Tokyo, 1993, pp. 31-45.

The number of atoms in the surface plane is one factor controlling the etching rate and subsequent development of surface morphology



The EBSD map tells us which crystallographic planes meet the surface. This information provides insight into the evolution of the surface features revealed by etching and their relationship to the underlying texture.

Zoom to the Red Circle



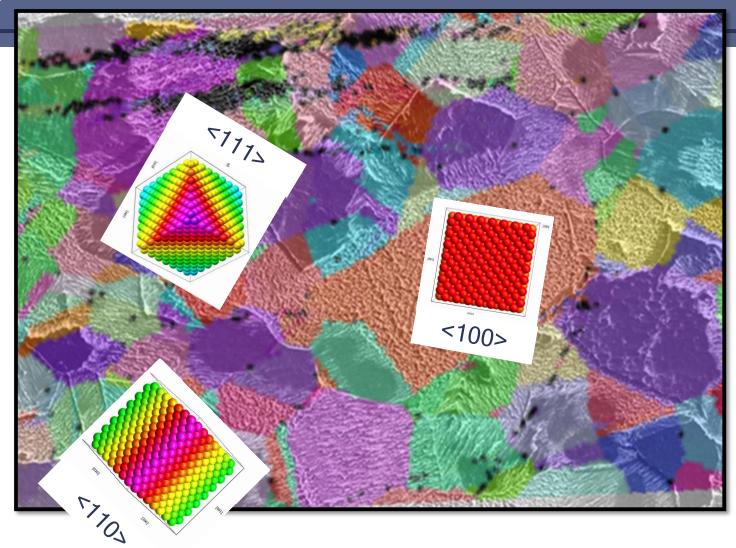


Overlay

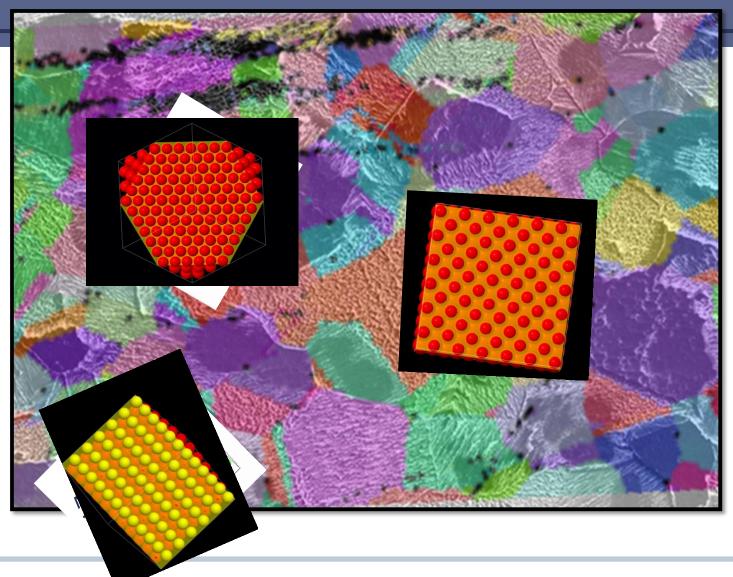




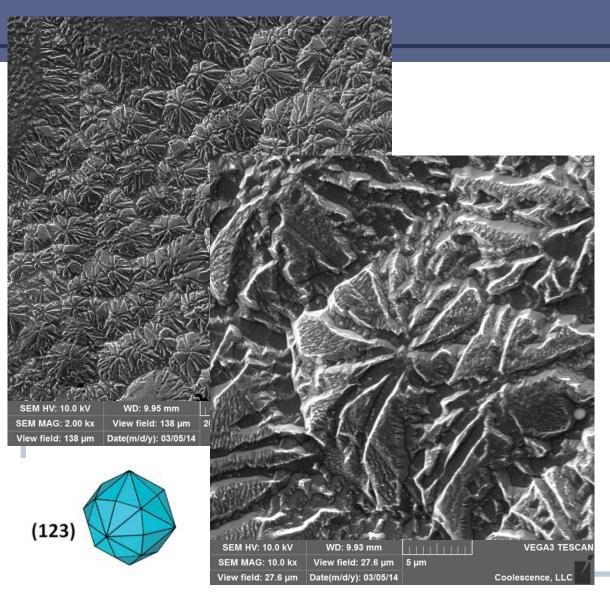
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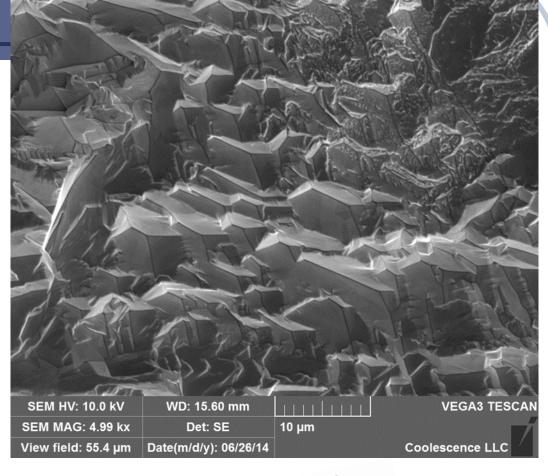


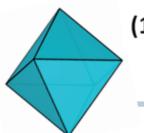
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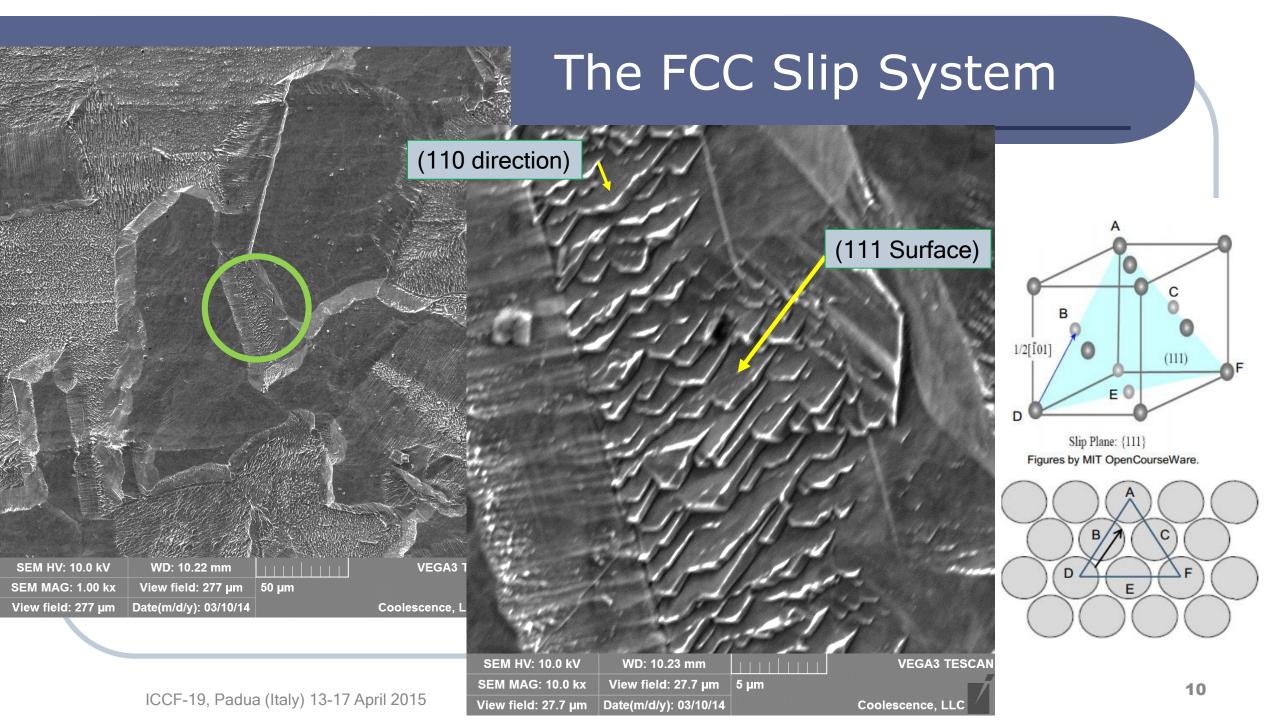
Palladium Facets Revealed by Etching







(111)



Strong Cube Texture "Recipe"

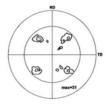
The as deformed texture components should be in the range:

S+C > 2B

 $S = \{123\} < 63\overline{4} > Slip deformation texture$

 $C = \{112\} < 111 > Copper texture$

 $B = \{110\} < 112 > Brass texture$



{111} pole figure for 99.987 pure palladium after Rolling (98.6%) and annealing at 850° for 1 h

If this case is met, strong cube text is reported after 850° C anneal for 1 hour with a grain size of 120 μm¹.

Roll Texture/No Dominant Orientation

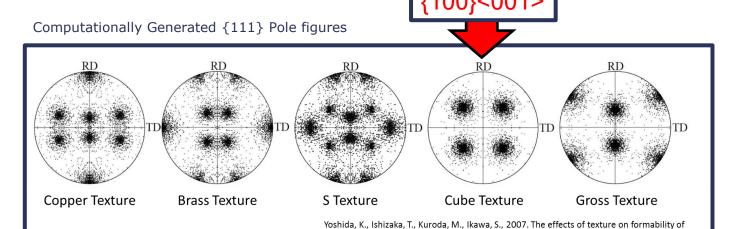
Name Indices Bunge (φ₁, 0, 0₂) Δ copper {112}<11√1> 90°, 35°, 45° • S1 {124}<21√1> 59°, 29°, 63° • S2 {123}<41√2> 47°, 37°, 63° • S3³ {123}<63√4> 59°, 37°, 63° • brass {110}<√12> 35°, 45°, 0° Taylor {4 4 11}<11 1√18> 7°, 71°, 70° ■ Goss {110}<01> 0°, 45°, 0°

Typical Textures: Thermomechanical Processing (TMP) of Metals, 27-750, Spring 2006 Advanced Characterization and Microstructural Analysis, A.D. Rollett, P. Kalu, D. Waryoba

Pole Figure Key

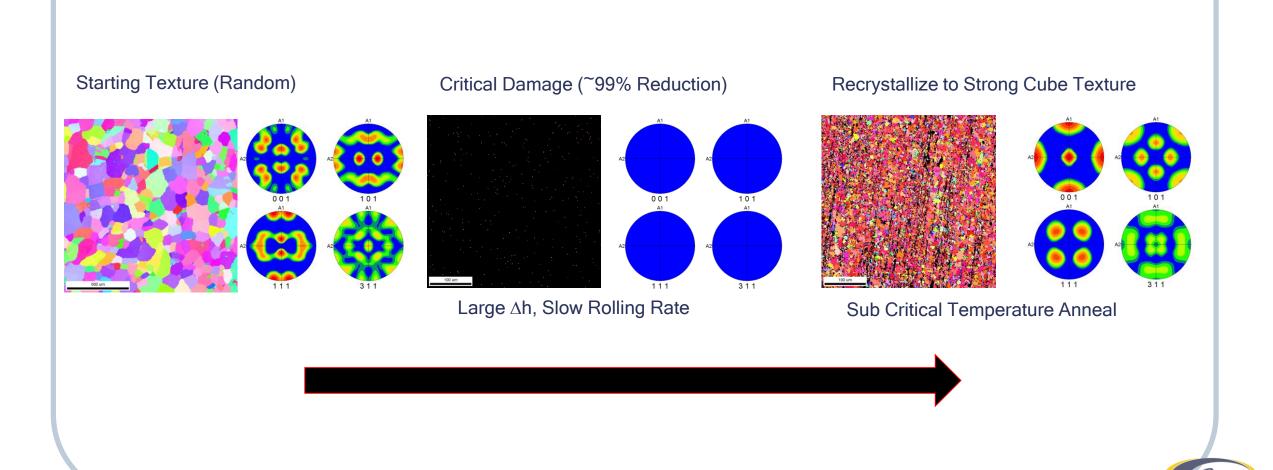
Strong Cube Texture

aluminum alloy sheets, Acta Materialia, 55 (13), 4499-4506



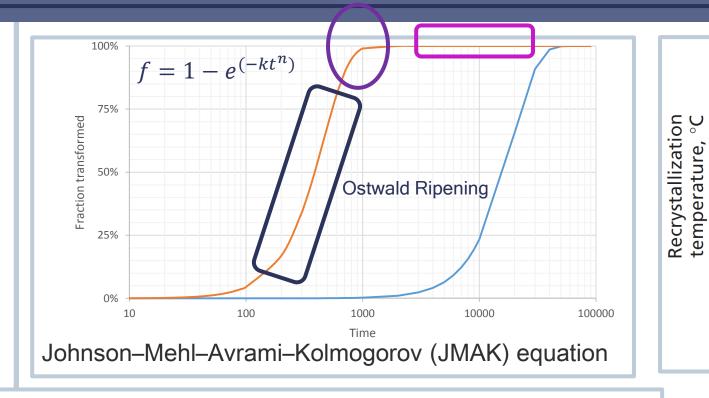
Strong cube textured methodology

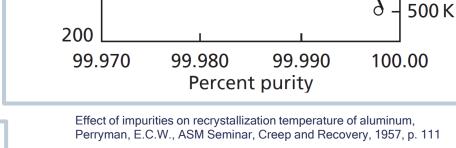
(best practices)



Recrystallization/Grain Growth

Normal Growth ~ t1/2 Impingement





High Purity Aluminum

0

450

400

350

300

250

temperature,

Driving force for grain growth ΔG

$$\Delta G = E_{grain\ boundaries} + \ E_{stacking\ faults} + \ E_{dislocation} + E_{surface\ energy} + E_{elastic\ strain} + ... + E_{zener\ pinning}$$

Microstructural evolution is in part controlled by the compilation of different sources of stored energy in the as-rolled material. ΔG acts to modify the activation energy in either direction.

Two main theories have been proposed for the formation of recrystallization textures. One of these suggests that the recrystallization texture is determined by the orientations of the nuclei formed, and the other, by the orientation-dependence of the rate of growth of the nuclei.

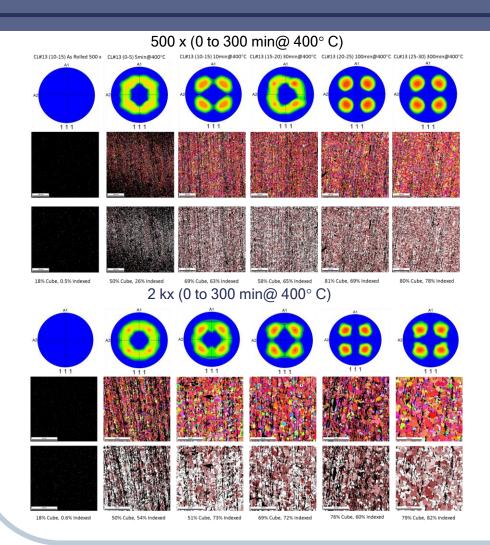
700 K

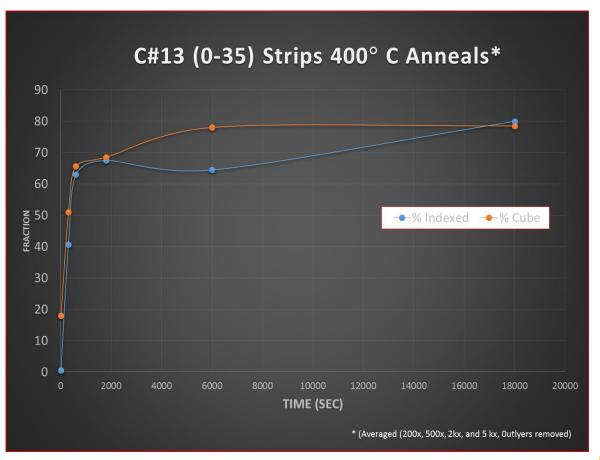
650 K

600 K

550 K

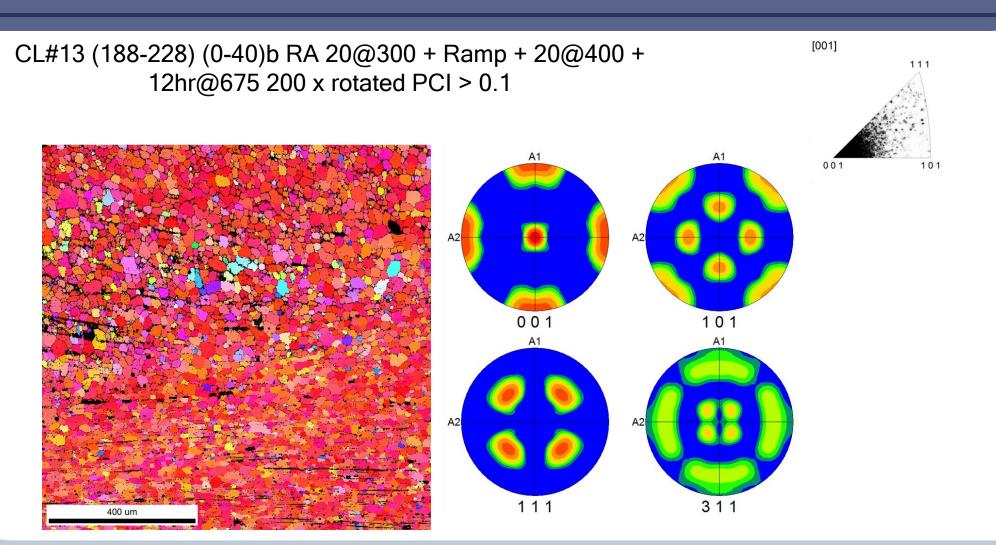
Seed Strong Cube Texture





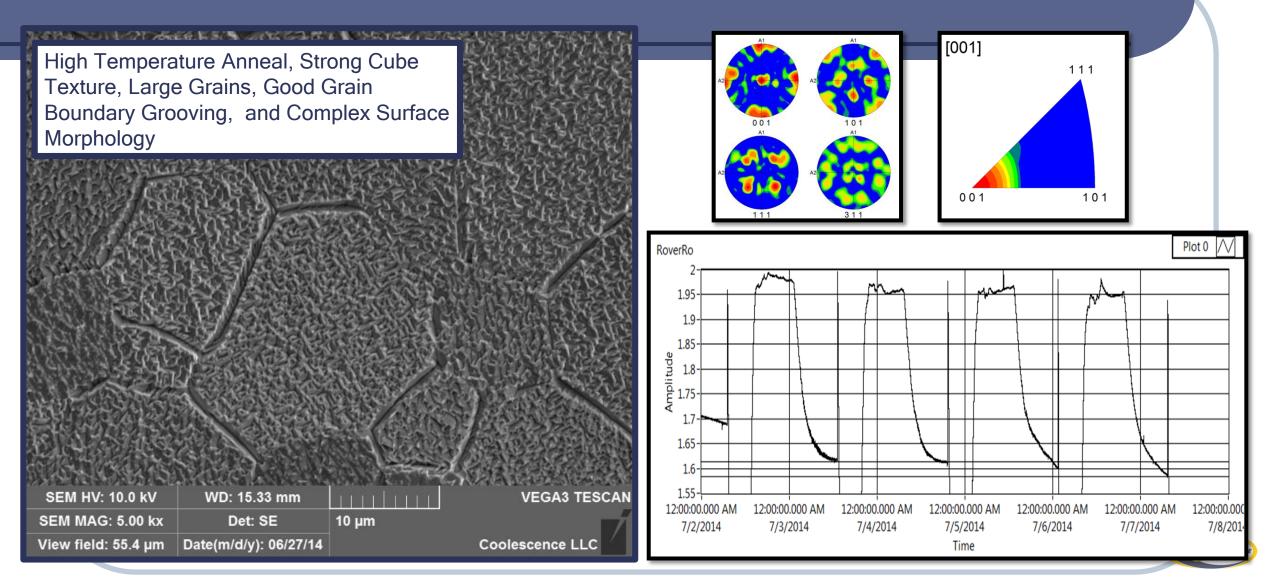


Requires Develop Lot Dependent Annealing Protocol

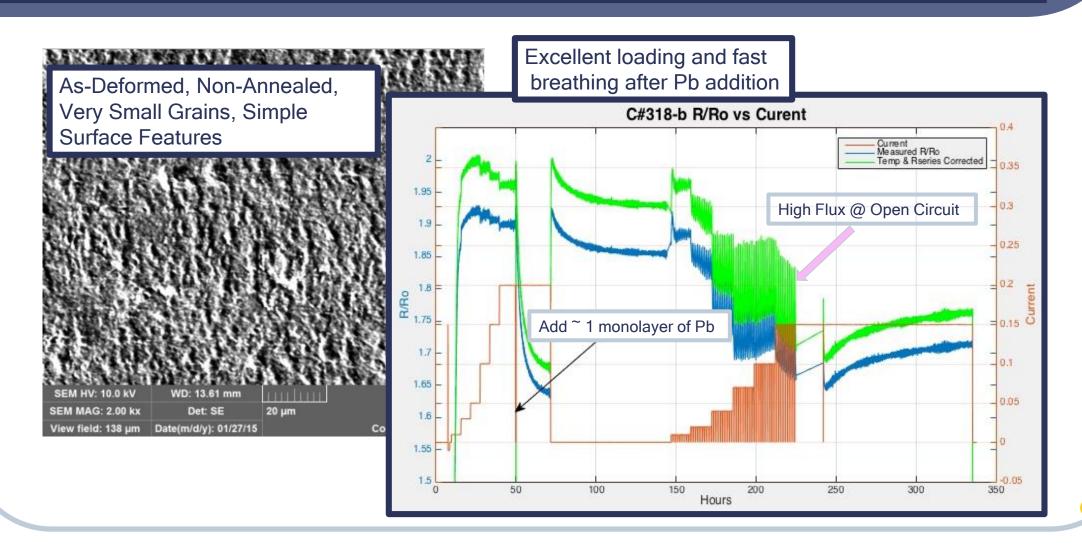




The Perfect Foil: C#255 RAE is from Pd Ingot#3 Part#1



The Anti-foil C#318



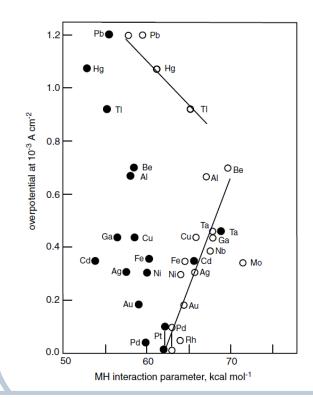


Electrochemical Performance

- I. Disconnect between high loading and metallurgical treatment
- As-deformed (non-annealed) foils are just as likely meet or exceed the loading threshold as highly textured foils.
- III. The primary predictor of high loading was determined to be the presence of non-uniform thin coatings (< 10 nm) of various surface promoters (Cu, Pb, In, Bi, and etc.)



Overpotential Equivalent HER



Exchange current density [A cm⁻²]

$$J_{Tot} = \sum_{i}^{n} J_{oi}(C_R e^{\beta f \eta} - C_O e^{-(1-\beta)f \eta})$$

 J_{Tot} = Total current density [A cm⁻²]

 J_{oi} = Exchange current density [A cm⁻²]

C_i = Concentration(t)/Concentration(t=0)

 β = Symmetry coefficient

 $f = F/RT [V^{-1}] @25 C \sim 38.9 V^{-1}$

 η = Overpotential [V] from Equilibrium Potential

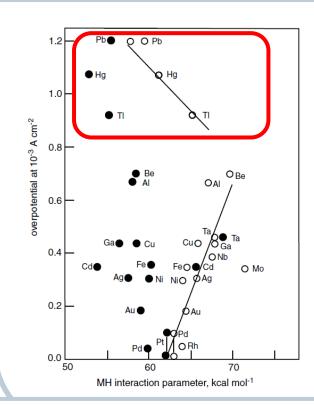
Electric Circuit Analogy

Plot of hydrogen overpotential at 10⁻³ A cm⁻² as function of metal-H interaction energy parameter¹

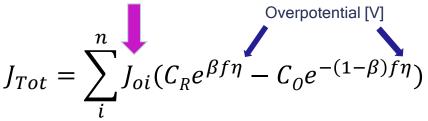
Under galvanostat control as surface coatings form, the overpotential must be increased to maintain constant current

Overpotential Equivalent HER

Red (High) - Pb, Hg, Ti (Basic Metals)



Exchange current density [A cm⁻²]



 J_{Tot} = Total current density [A cm⁻²]

 J_{oi} = Exchange current density [A cm⁻²]

C_i = Concentration(t)/Concentration(t=0)

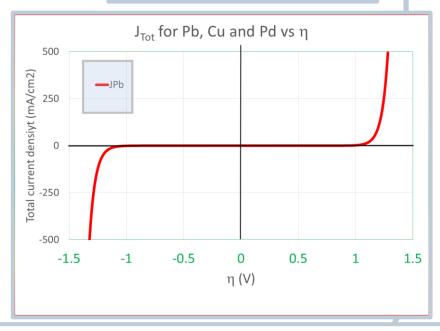
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Electric Circuit Analogy

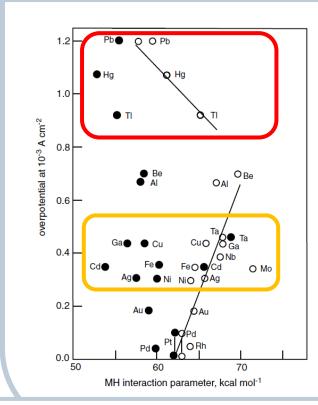


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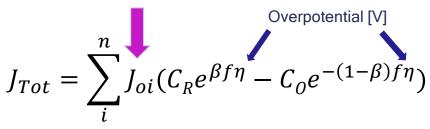
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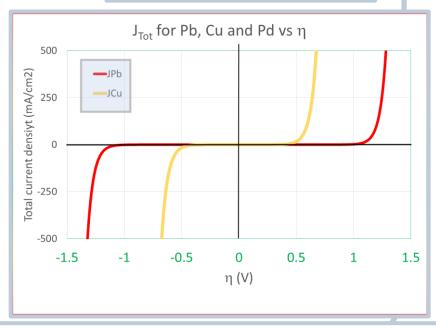
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Electric Circuit Analogy

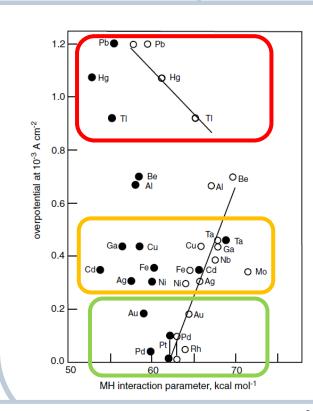


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Red (High) - Pb, Hg, Ti (Basic Metals)
Yellow(Medium) - Cu, Fe, Ni (Light Transition Metals)
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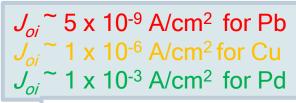
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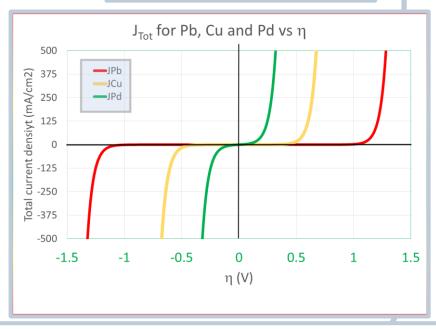
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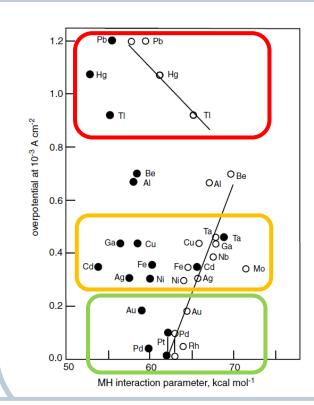


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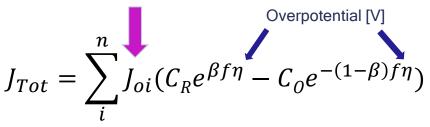
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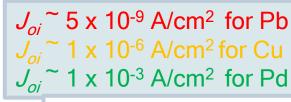
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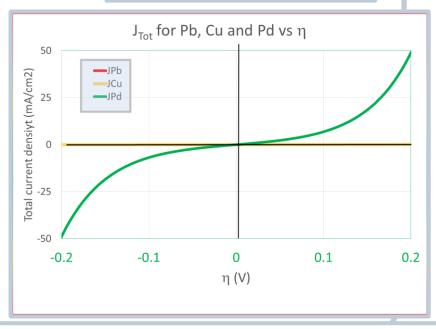
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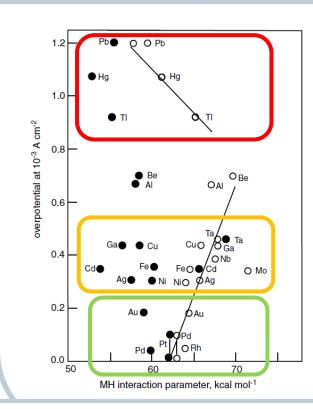


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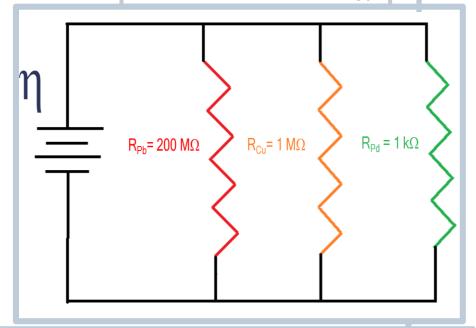
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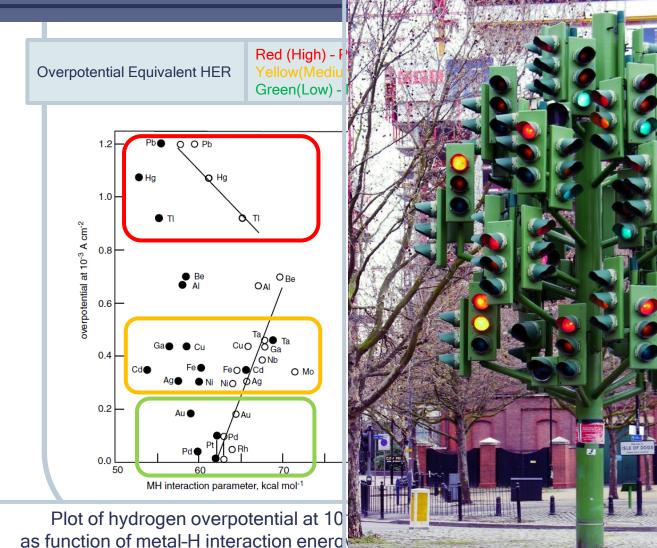


Electric Circuit Analogy



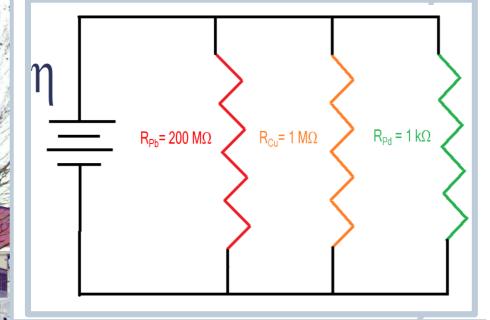
Plot of hydrogen overpotential at 10⁻³ A cm⁻² as function of metal-H interaction energy parameter¹

Under galvanostat control as surface coatings form, the overpotential must be increased to maintain constant current



 J_{oi} $\sim 5 \times 10^{-9} \text{ A/cm}^2 \text{ for Pb}$ J_{oi} $\sim 1 \times 10^{-6} \text{ A/cm}^2 \text{ for Cu}$ J_{oi} $\sim 1 \times 10^{-3} \text{ A/cm}^2 \text{ for Pd}$

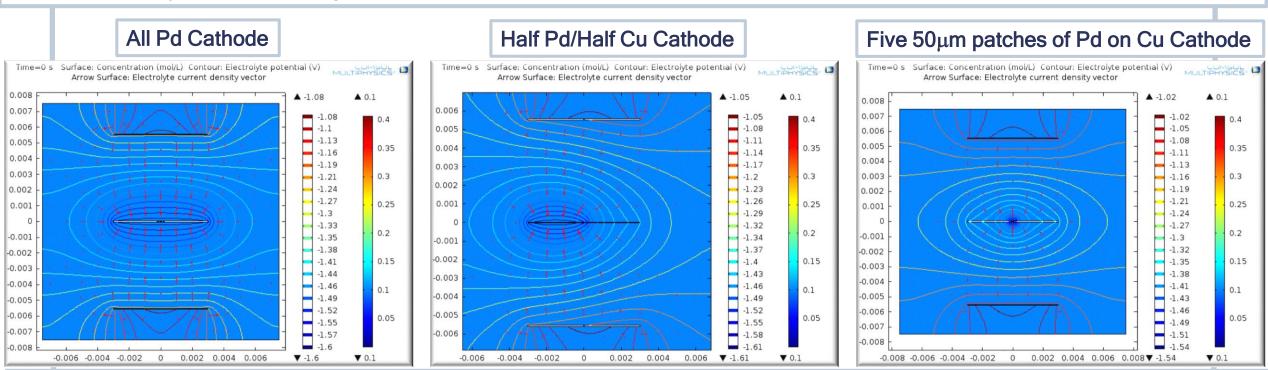
Electric Circuit Analogy



r galvanostat control as surface coatings form, the ential must be increased to maintain constant current

Electrofocusing increasing the local OD concentration

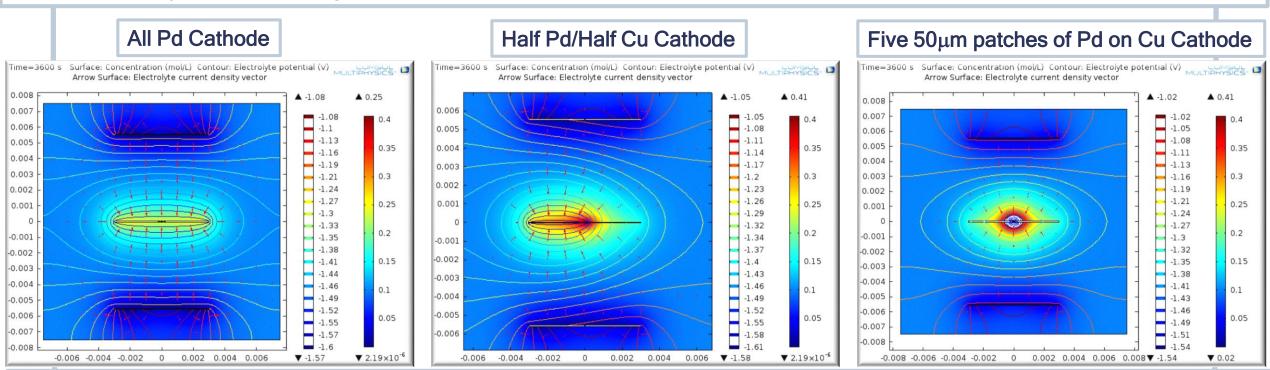
ii. What we are calling surface promoters would normally be thought of as poisons; however, in our voltaic cells the limiting current occurs when the local concentration of OD- at the anode goes to zero. Therefore, it is possible to focus nearly all of the charge transfer/current on exposed palladium islands.



The red arrows show both the magnitude and direction for the current distribution. The electrolyte potential is shown by the contour lines (-1.6 to -1.08 V). The OH- concentration is given by the fill color (dark blue is zero and red represents 400 mM).

Electrofocusing increasing the local OD concentration

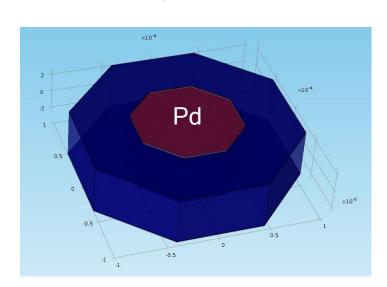
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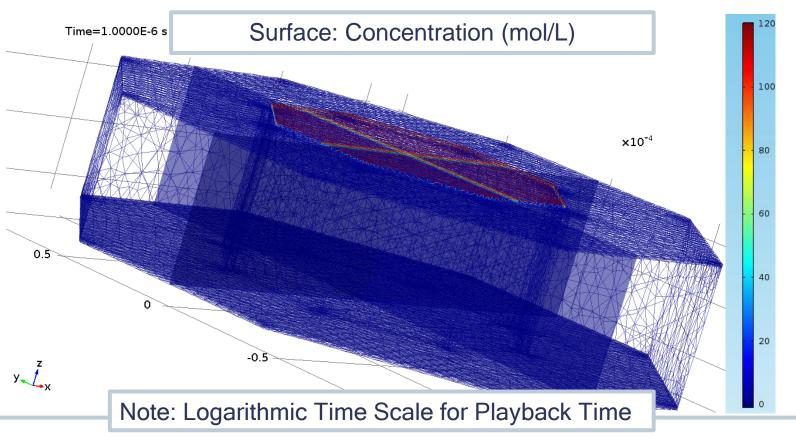
The red arrows show both the magnitude and direction for the current distribution. The electrolyte potential is shown by the contour lines (-1.6 to -1.08 V). The OH- concentration is given by the fill color (dark blue is zero and red represents 400 mM).

Deuterium enters bulk through Pd Islands

- III. The diffusion coefficient for palladium is large enough that only a small fraction of the cathode need be open to achieve high bulk loading.
- IV. Select promoter impurities can function as both spillover and reverse spillover catalysts. We believe this explains the extraordinary flux seen with Cu islands and reduced flux on Pb doped cathodes. (S. Hamm and O. Dmitriyeva posters)

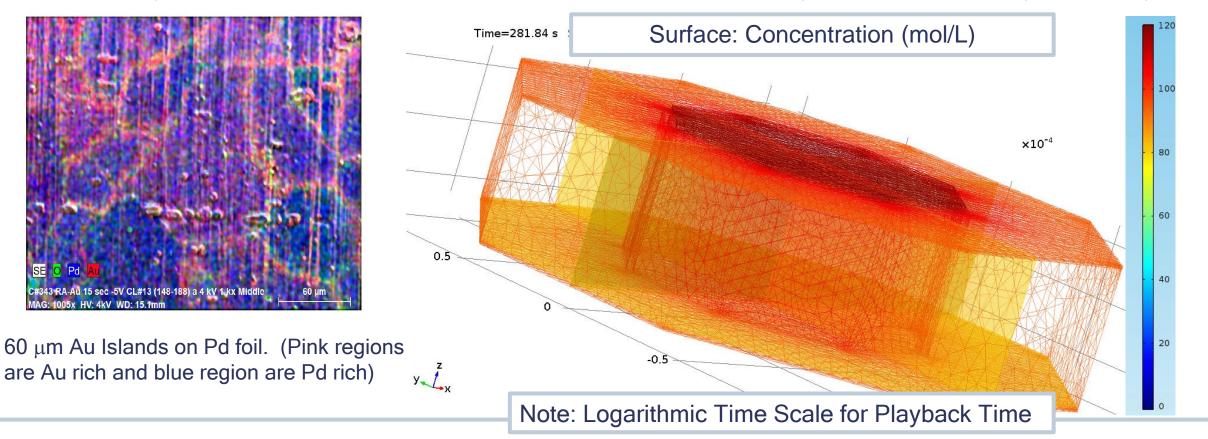


 $200~\mu m$ Grain with $50~\mu m$ Pd island with the D concentration set to 100~mol/L



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Summary

- I. A methodology to control the crystallographic texture and grain size of palladium foils was demonstrated
- II. Select surface promoters¹ near a monolayer in thickness are first order factors controlling loading
 ∴ Nanomolar intentional or accidental additions must be controlled!
- III. Loading appears to be nearly independent of metallurgical treatment
 - a) Grain size, grain boundary grooving, annealing time and temperature, cracks formed along the {111} slip planes in the 〈011〉 slip directions, loading protocols (constant current, voltage control, and rate of change of either) are all second order effects at best
 - b) As-rolled (non-annealed) foils perform similarly to annealed foils from a loading standpoint. (See S. Hamm and O. Dmitriyeva presentations for more details on this topic)
- IV. This finding does not rule out the potential importance of grain size, crystallographic texture, and grain boundary type to the production of excess heat from the deuterium-palladium system.



